20V Repetitive Peak Reverse Voltage SS12A Schottky Barrier Diode SMA Package

Basic Information

• Place of Origin: Shenzhen, Guangdong, China

• Brand Name: SOCAY

Certification: REACH,RoHS,ISO

Model Number: SS12A
Minimum Order Quantity: 5000PCS
Price: Negotiable
Delivery Time: 5-8 work days



Product Specification

Component Name: Schottky Barrier Diode

• Package Type: DO-214AC(SMA)

VRRM: 20V
VRMS: 14V
VDC: 20V
IF(AV): 1A
IFSM: 40A
Dv/dt: 10000V/µs



Product Description

20V Repetitive Peak Reverse Voltage SS12A Schottky Barrier Diode SMA Package

Schottky Barrier Diode DATASHEET: SS12A~SS120A(SMA)_v2211.1.pdf

Schottky Barrier Diode Features:

Low profile package

Ideal for automated placement

Ultrafast reverse recovery time

Low power losses, high efficiency

Low forward voltage drop

High surge capability

High temperature soldering:

260 /10 seconds at terminals

Component in accordance to RoHS 2002/95/1 and WEEE 2002/96/EC

Schottky Barrier Diode Mechanical Data:

Case: JEDEC DO-214AC molded plastic

Terminals: Solder plated, solderable per J-STD-002B and JESD22-B102D

Polarity: Laser band denotes cathode end

Schottky Barrier Diode Major Ratings and Characteristics:

I _{F(AV)}	1.0A
V _{RRM}	20 V to 200 V
I _{FSM}	40A
V _F	0.50V, 0.55V, 0.70V, 0.85V,0.95V
T _{j max} .	125

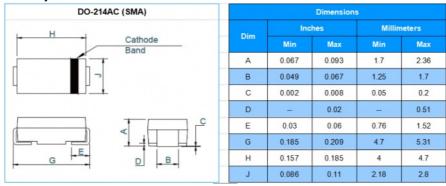
Schottky Barrier Diode Maximum Ratings & Thermal Characteristics(T_A = 25 unless otherwise noted):

	7			1			1		1	1	
Items	Symb ol	l .	ı	SS14 A	SS15 A	SS16 A	1		SS11 5A	SS120 A	Unit
Maximum repetitive peak reverse voltage		20	30	40	50	60	80	100	150	200	v
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	105	140	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	150	200	V
Maximum average forward rectified current	I _{F(AV)}	1									A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I _{ESM}	40									A
Voltage rate of change (rated V _R)	dv/dt	10000									V/µs
Thermal resistance from junction to lead (1)	1	35									/W
remperature range	T _J ,T _{ST} G	-65 10									
Note 1: Mounted on P.C.B. with 0.2 x 0.2" (5.0 x 5.0mm) copper pad areas.											

Schottky Barrier Diode Electrical Characteristics (T_A = 25 unless otherwise noted):

, ,											
Items	Test con	ditions	Symbol	SS12A	SS13A~ SS14A	SS15A~ SS16A	SS18A~ SS110A	SS115A~ SS120A	Unit		
Instantaneous forward voltage	IF=1.0A(2)		VF	0.50	0.55	0.70	0.85	0.95	V		
Reverse current	VR=VDC	Tj=25	IR	0.5					mΑ		
		Tj=100		5.0							
Note 2: Pulse test:300µs pulse width,1% duty cycle.											

Schottky Barrier Diode SS12A Diode Dimensions:



Schottky Barrier Diode SS12A Notice:

Product is intended for use in general electronics applications.

Product should be worked less than the ratings; if exceeded, may cause permanent damage, or introduce latent failure mechanisms.

The absolute maximum ratings are rated values and must not be exceeded during operation. The following are the general derating methods you design a circuit with a device.

 $I_{F(AV)}$: We recommend that the worst case current be no greater than 80% .

I_{FSM}: This rating specifies the non-repetitive peak current. This is only applied for an abnormal operation, which the general during the lifespan of the device.

T_J: Derate this rating when using a device in order to ensure high reliability. We recommend that the device be used at a Tof below 100.











GuangDong Province, China